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(74) Agent: SHINDLER, Nigel; Brookes Batchellor, 102-108 Clerkenwell Road, London EC1M 5SA (GB).

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- (71) Applicant (for all designated States except US): IM-PERIAL COLLEGE INNOVATIONS LIMITED [GB/GB]; Level 12, Electrical Engineering Building, Imperial College London, Exhibition Road, London SW7 2BT (GB).
- (72) Inventor; and
- (75) Inventor/Applicant (for US only): GREEN, Mino [GB/GB]; 55 Gerard Road, Barnes, London SW13 9QH (GB).

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(54) Title: STRUCTURED SILICON ANODE

(57) Abstract: A silicon/lithium battery which can be fabricated from a silicon substrate allowing it to be produced as an integrated unit on a chip, the battery comprising a silicon anode formed from sub-micron diameter pillars of silicon fabricated on an n-type silicon wafer.